MPS4250

Transistor

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	-40	Vdc
Collector - Emitter Voltage	V _{CES}	-40	Vdc
Collector - Base Voltage	V _{CBO}	-40	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	I _C	-	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	W mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

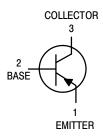
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



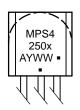
ON Semiconductor®

http://onsemi.com



MARKING DIAGRAM





MPS4250x = Device Code

 $x = A^*$

*MPS4250ARLRM

*MPS4250ARLRMG

A = Assembly Location

Y = Year
WW = Work Week

Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MPS4250	TO-92	5000/Tape & Reel
MPS4250G	TO-92 (Pb-Free)	5000/Tape & Reel
MPS4250ARLRM	TO-92	2000/Tape & Ammo
MPS4250ARLRMG	TO-92 (Pb-Free)	2000/Tape & Ammo

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MPS4250

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

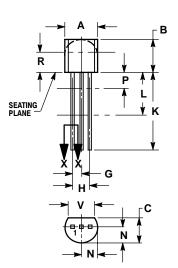
Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I _C = −5.0 mA)	V _(BR) CES	-40	_	Vdc
Collector – Emitter Sustaining Voltage (Note 1) $(I_C = -5.0)$	V _(BR) CEO(sus)	-40	-	Vdc
Collector – Base Breakdown Voltage $(I_C = -10 \mu A)$	V _(BR) CBO	-40	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu A$)	V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = -50 \text{ V})$ $(V_{CB} = -40 \text{ V}, T_A = 65^{\circ}\text{C})$	I _{CBO}	- -	-10 -3.0	nA μA
Emitter Cutoff Current (V _{EB} = -3.0 V)	I _{EBO}	-	-20	nA
ON CHARACTERISTICS				
DC Current Gain $(I_C = -1.0 \text{ mA}, V_{CE} = -5.0 \text{ V})$ $(I_C = -10 \text{ mA}, V_{CE} = -5.0 \text{ V})$	h _{FE}	250 250	_ _	_
Collector – Emitter Saturation Voltage (Note 1) $(I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA})$	V _{CE(sat)}	-	-0.25	Vdc
Base – Emitter Saturation Voltage (Note 1) ($I_C = -10 \text{ mA}, I_B = -0.5 \text{ mA}$)	V _{BE(sat)}	-	-0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS	-			
Output Capacitance $(V_{CB} = -5.0 \text{ V}, f = 1.0 \text{ MHz})$	C _{obo}	-	6.0	pF
Input Capacitance $(V_{EB} = -0.5 \text{ V}, f = 1.0 \text{ MHz})$	C _{ibo}	-	16	pF
Small–Signal Current Gain ($I_C = -1.0$ mA, $V_{CE} = -5.0$ V, $f = 1.0$ kHz) ($I_C = -0.5$ mA, $V_{CE} = -5.0$ V, $f = 20$ MHz)	h _{fe}	250 2.0	800	-
Noise Figure $ \begin{array}{l} \text{(I}_{C}=-20~\mu\text{A, V}_{CE}=-5.0~\text{V, R}_{S}=10~\text{k}\Omega,f=1.0~\text{kHz, P}_{BW}=150~\text{Hz)} \\ \text{(I}_{C}=-250~\mu\text{A, V}_{CE}=-5.0~\text{V, R}_{S}=1.0~\text{k}\Omega,f=1.0~\text{kHz, P}_{BW}=150~\text{Hz)} \end{array} $	NF	- -	2.0 2.0	dB

^{1.} Pulse Test: Pulse Width = 300 µs; Duty Cycle = 2.0%.

MPS4250

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 114-3M, 1902.
 CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R
 IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 1:

PIN 1. EMITTER

BASE 2.

COLLECTOR

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